

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor device comprising:
~~a first conductive layer over an insulating surface;~~
~~a second conductive layer on said first conductive layer wherein a width of the second conductive layer is narrower than that of the first conductive layer;~~
~~an insulating film over the second conductive layer;~~
a semiconductor region ~~over the insulating film, the semiconductor region~~ comprising a source region, a drain region, a channel region, and a pair of regions between the channel region and the source and drain regions, said pair of regions formed of a same material as said channel region wherein each of said pair of regions has a first portion contiguous to the channel region and a second portion contiguous to the source or drain regions;
a gate insulating film adjacent to said semiconductor region;
a first conductive layer adjacent to the channel region and having the gate insulating film interposed therebetween; and
a second conductive layer formed adjacent to said first conductive layer, such that the first conductive layer is between the gate insulating film and the second conductive layer, wherein a width of the first conductive layer is narrower than that of the second conductive layer;
wherein the ~~second~~ first conductive layer extends beyond side edges of the ~~first~~ second conductive layer and extending portions of the ~~second~~ first conductive layer overlap the first portions of said pair of regions while the second portions are not overlapped by said ~~second~~ first conductive layer, and
wherein the semiconductor device forms a bottom gate type transistor in which the first conductive layer and the second conductive layer are located below the semiconductor region.

2-43. (Cancelled)

44. (Currently Amended) A semiconductor device comprising:

~~a first conductive layer over an insulating surface;~~

~~a second conductive layer on said first conductive layer wherein a width of the second conductive layer is narrower than that of the first conductive layer;~~

~~an insulating film over the second conductive layer;~~

~~a semiconductor region over the insulating film, the semiconductor region comprising a source region, a drain region, a channel region, and a pair of regions between the channel region and the source and drain regions, said pair of regions formed of a same material as said channel region wherein each of said pair of regions has a first portion contiguous to the channel region and a second portion contiguous to the source or drain regions;~~

a gate insulating film formed adjacent to the semiconductor region;

a first conductive layer adjacent to the channel region and having the gate insulating film interposed therebetween; and

a second conductive layer formed adjacent to the first conductive layer, such that the first conductive layer is between the gate insulating film and the second conductive layer, wherein a width of the first conductive layer is narrower than that of the second conductive layer,

wherein the second ~~first~~ conductive layer extends beyond side edges of the first ~~second~~ conductive layer and extending portions of the second ~~first~~ conductive layer overlap the first portions of said pair of regions while the second portions are not overlapped by said second ~~first~~ conductive layer, and

wherein the semiconductor device forms a bottom gate type transistor in which the first conductive layer and the second conductive layer are located below the semiconductor region,
and

wherein the first conductive layer and the second conductive layer are different materials
~~material each other.~~

45. (Currently Amended) A semiconductor device comprising:
~~a first conductive layer over an insulating surface;~~
~~a second conductive layer on said first conductive layer wherein a width of the second~~
~~conductive layer is narrower than that of the first conductive layer;~~
~~an insulating film over the second conductive layer;~~
a semiconductor region ~~over the insulating film, the semiconductor region~~ comprising a source region, a drain region, a channel region, and a pair of regions between the channel region and the source and drain regions, said pair of regions formed of a same material as said channel region wherein each of said pair of regions has a first portion contiguous to the channel region and a second portion contiguous to the source or drain regions;
a gate insulating film formed adjacent to the semiconductor region;
a first conductive layer adjacent to the channel region and having the gate insulating film interposed therebetween; and
a second conductive layer formed adjacent to the first conductive layer, such that the first
conductive layer is between the gate insulating film and the second conductive layer, wherein a
width of the first conductive layer is narrower than that of the second conductive layer,
wherein the second ~~first~~ conductive layer extends beyond side edges of the first conductive layer and extending portions of the second ~~first~~ conductive layer overlap the first portions of said pair of regions while the second portions are not overlapped by said second ~~first~~ conductive layer, and
wherein the semiconductor device forms a bottom gate type transistor in which the first
conductive layer and the second conductive layer are located below the semiconductor region,
and
wherein a distance between the first portion and the source or drain region is larger than a thickness of the first ~~second~~ conductive layer.

46. (Cancelled)

47. (Currently Amended) A semiconductor device comprising:

- ~~a first conductive layer over an insulating surface;~~
- ~~a second conductive layer on said first conductive layer wherein a width of the second conductive layer is narrower than that of the first conductive layer;~~
- ~~an insulating film over the second conductive layer;~~
- a semiconductor region ~~over the insulating film, the semiconductor region~~ comprising a source region, a drain region, a channel region, and a pair of regions between the channel region and the source and drain regions, said pair of regions formed of a same material as said channel region wherein each of said pair of regions has a first portion contiguous to the channel region and a second portion contiguous to the source or drain regions;
- a gate insulating film formed adjacent to the semiconductor region;
- a first conductive layer adjacent to the channel region and having the gate insulating film interposed therebetween; and
- a second conductive layer formed adjacent to the first conductive layer, such that the first conductive layer is between the gate insulating film and the second conductive layer, wherein a width of the first conductive layer is narrower than that of the second conductive layer,

wherein the second ~~first~~ conductive layer extends beyond side edges of the first ~~second~~ conductive layer and extending portions of the second ~~first~~ conductive layer overlap the first portions of said pair of regions while the second portions are not overlapped by said second ~~first~~ conductive layer, and

wherein the semiconductor device forms a bottom gate type transistor in which the first conductive layer and the second conductive layer are located below the semiconductor region,

and

wherein a distance between the first portion and the source or drain region is equal to or less than a thickness of the second conductive layer.

48. (Currently Amended) A semiconductor device comprising:

- ~~a first conductive layer over an insulating surface;~~

~~a second conductive layer on said first conductive layer wherein a width of the second conductive layer is narrower than that of the first conductive layer;~~

~~an insulating film over the second conductive layer;~~

a semiconductor region ~~over the insulating film, the semiconductor region~~ comprising a source region, a drain region, a channel region formed on an insulating surface, and a pair of regions between the channel region and the source and drain regions, said pair of regions formed of a same material as said channel region wherein each of said pair of regions has a first portion contiguous to the channel region and a second portion contiguous to the source or drain regions;

a gate insulating film formed adjacent to the semiconductor region;

a first conductive layer adjacent to the channel region and having the gate insulating film interposed therebetween; and

a second conductive layer formed adjacent to the first conductive layer, such that the first conductive layer is between the gate insulating film and the second conductive layer, wherein a width of the first conductive layer is narrower than that of the second conductive layer,

wherein the second ~~first~~ conductive layer extends beyond side edges of the first ~~second~~ conductive layer and extending portions of the second ~~first~~ conductive layer overlap the first portions of said pair of regions while the second portions are not overlapped by said second ~~first~~ conductive layer, and

wherein the semiconductor device forms a bottom gate type transistor in which the first conductive layer and the second conductive layer are located below the semiconductor region,
and

wherein a distance between the first portion and the source or drain region is equal to or less than a thickness of the ~~second~~ first conductive layer.

49-54. (Cancelled)

55. (Previously presented) A semiconductor device according to ~~claims~~ claim 1,

wherein each of the first and second conductive layers comprises a material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt.

56. (Previously presented) A semiconductor device according to ~~claims~~ claim 44, wherein each of the first and second conductive layers comprises a material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt.

57. (Previously presented) A semiconductor device according to ~~claims~~ claim 45, wherein each of the first and second conductive layers comprises a material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt.

58. (Cancelled)

59. (Previously presented) A semiconductor device according to ~~claims~~ claim 47, wherein each of the first and second conductive layers comprises a material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt.

60. (Previously presented) A semiconductor device according to ~~claims~~ claim 48, wherein each of the first and second conductive layers comprises a material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt.

61. (Currently Amended) A semiconductor device according to claim 1,

wherein a distance between the first portion and the source or drain region is 500 Å 500 Å
to 1000.1000 Å.

62. (Currently Amended) A semiconductor device according to claim 44,
wherein a distance between the first portion and the source or drain region is 500 Å 500 Å
to 1000.1000 Å.

63. (Currently Amended) A semiconductor device according to claim 45,
wherein a distance between the first portion and the source or drain region is 500 Å 500 Å
to 1000.1000 Å.

64. (Cancelled)

65. (Currently Amended) A semiconductor device according to claim 47,
wherein a distance between the first portion and the source or drain region is 500 Å 500 Å
to 1000.1000 Å.

66. (Currently Amended) A semiconductor device according to claim 48,
wherein a distance between the first portion and the source or drain region is 500 Å 500 Å
to 1000.1000 Å.

67. (Previously presented) A semiconductor device according to claim 1, wherein said
insulating film comprises silicon oxide.

68. (Previously presented) A semiconductor device according to claim 44, wherein said
insulating film comprises silicon oxide.

69. (Previously presented) A semiconductor device according to claim 45, wherein said insulating film comprises silicon oxide.

70. (Cancelled)

71. (Previously presented) A semiconductor device according to claim 47, wherein said insulating film comprises silicon oxide.

72. (Previously presented) A semiconductor device according to claim 48, wherein said insulating film comprises silicon oxide.

73. (Previously presented) A semiconductor device according to claim 1, wherein said ~~second~~ first conductive layer comprises tantalum and said ~~first~~ second conductive layer comprises aluminum.

74. (Previously presented) A semiconductor device according to claim 44, wherein said ~~second~~ first conductive layer comprises tantalum and said ~~first~~ second conductive layer comprises aluminum.

75. (Previously presented) A semiconductor device according to claim 45, wherein said ~~second~~ first conductive layer comprises tantalum and said ~~first~~ second conductive layer comprises aluminum.

76. (Cancelled)

77. (Previously presented) A semiconductor device according to claim 47, wherein said ~~second~~ first conductive layer comprises tantalum and said ~~first~~ second conductive layer comprises aluminum.

78. (Previously presented) A semiconductor device according to claim 48, wherein said ~~second~~ first conductive layer comprises tantalum and said ~~first~~ second conductive layer comprises aluminum.

79. (Previously presented) A semiconductor device according to claim 1, wherein the semiconductor region comprises crystalline silicon.

80. (Previously presented) A semiconductor device according to claim 44, wherein the semiconductor film comprises crystalline silicon.

81. (Previously presented) A semiconductor device according to claim 45, wherein the semiconductor region comprises crystalline silicon.

82. (Cancelled)

83. (Previously presented) A semiconductor device according to claim 47, wherein the semiconductor region comprises crystalline silicon.

84. (Previously presented) A semiconductor device according to claim 48, wherein the semiconductor film comprises crystalline silicon.